L # Hits DBs Time Stamp Type Search Text USPAT; 2002/01/07 1 BRS L1145 438/142 EPO; 08:51 JPO USPAT; semiconductor adj side adj 2002/01/07 EPO; 2 BRS 1.2 wall adj fin 08:53 JPO USPAT; 2002/01/07 103 side adj wall adj fin EPO; 3 BRS L3 08:54 JPO USPAT; 2002/01/07 EPO; 4 BRS L4 575 wall adj fin 08:54 JPO USPAT; 2002/01/07 10 5 BRS L5 / semiconductor adj fin EPO; 08:55 JPO USPAT; 2002/01/07 6 BRS L6 56541 fet EPO; 08:55 JPO USPAT; double adj gated adj field 2002/01/07 L7 L EPO: 7 BRS adj effect adj transistor 08:56 JPO USPAT; 2002/01/07 401 SOI adj MOSFET EPO; 8 BRS Γ 8 08:56 JPO USPAT; 2002/01/07 L9 33 9 BRS damascene adj gate EPO; 08:57 JPO USPAT; 2002/01/07 EPO; 10 BRS L10 103 3 and 408:57 JPO USPAT; 2002/01/07 1 and 3 EPO; 11 BRS L11 0 08:58 JPO USPAT; 2002/01/07 L12, 26 1 and 6 12 BRS EPO; 08:58 JPO

	Туре	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	0	3 and 6		2002/01/07 08:58
14	BRS	L14	0	3 and 8	; H P() *	2002/01/07 08:58
15	BRS	L15	146	6 and 8	USPAT; EPO; JPO	2002/01/07 08:58
16	BRS	L16	1	1 and 6 and 8	: H P() *	2002/01/07 08:59
17	BRS	L17	0	4 and 6 and 8	USPAT; EPO; JPO	2002/01/07 08:59

6,326,247 46,323,082 -6,303,479 -6,232,163 -6,159,778 -6,063,686 \$5,981,318	5,661,061	15 X	_5,349,228 -5,273,921	* * * - 一 *
*5,780,327 *5,780,327 *5,713,328 *5,736,437			•	

L9 [12 -6,333,247 -6,323,103 -6,333,229 -6,284,637 -6,329,256 +6,165,822 +6,291,278 +6,114,195 -6,271,132 +5,950,076 5,944,970 6,258,679